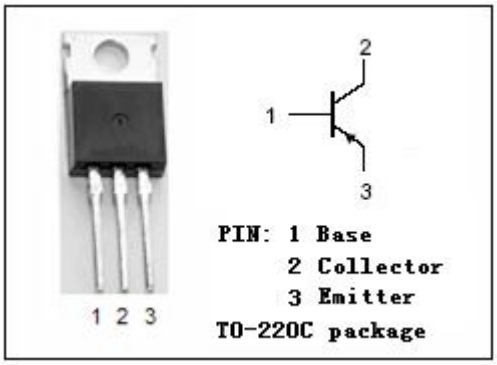
isc Silicon PNP Power Transistor — 2SB1037

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -150V(Min.)
- Wide Area of Safe Operation
- Complement to Type 2SD1459
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

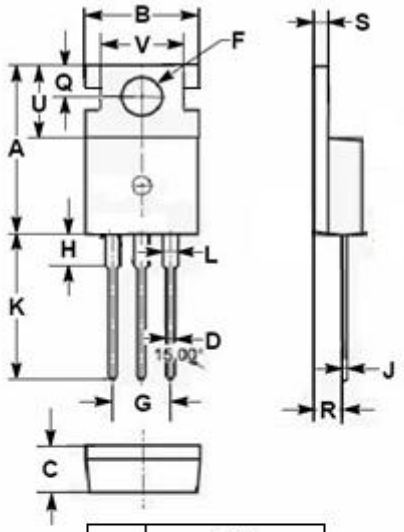


APPLICATIONS

- Designed for color TV vertical output, sound output applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-150	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-1.5	A
I_{CM}	Collector Current-Peak	-3	A
P_C	Total Power Dissipation @ T_C=25℃	30	W
	Total Power Dissipation @ T_a=25℃	2	
T_J	Junction Temperature	175	℃
T_{stg}	Storage Temperature Range	-55~175	℃



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

isc Silicon PNP Power Transistor 2SB1037

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -1mA; I_B= 0	-150			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -0.5A; I_B= -50mA			-1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -0.5A; I_B= -50mA			-1.2	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -120V; I_E= 0			-10	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-10	μA
h_{FE}	DC Current Gain	I_C= -0.3A; V_{CE}= -5V	70		200	
f_T	Current-Gain—Bandwidth Product	I_C= -0.1A; V_{CE}= -5V		15		MHz

◆ **h_{FE} Classifications**

Q	R
70-140	100-200